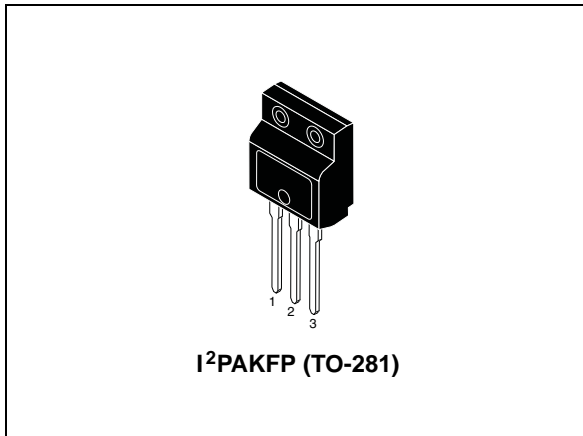
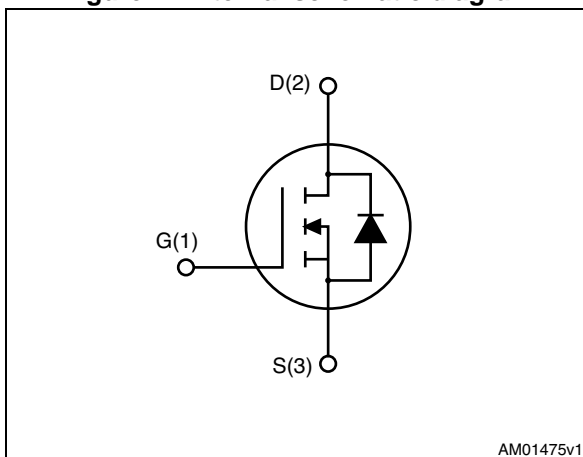


## N-channel 650 V, 15 A, 0.250 $\Omega$ typ., MDmesh™ II Power MOSFET in a I<sup>2</sup>PAKFP package

Datasheet - production data



**Figure 1. Internal schematic diagram**



### Features

Order code	V <sub>DSS</sub> @T <sub>jmax</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>
STFI20NM65N	710 V	0.270 $\Omega$	15 A

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

### Applications

- Switching applications

### Description

This device is an N-channel Power MOSFET developed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

**Table 1. Device summary**

Order code	Marking	Packages	Packaging
STFI20NM65N	20NM65N	I <sup>2</sup> PAKFP (TO-281)	Tube

# Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain source voltage	650	V
$V_{GS}$	Gate source voltage	$\pm 25$	V
$I_D$	Drain current continuous $T_C = 25\text{ }^\circ\text{C}$	15 <sup>(1)</sup>	A
$I_D$	Drain current continuous $T_C = 100\text{ }^\circ\text{C}$	9.45	A
$I_{DM}^{(2)}$	Drain current pulsed	60	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	30	W
$dv/dt^{(3)}$	Peak diode recovery voltage slope	15	V/ns
$V_{ISO}$	Insulation withstand voltage (RMS) from all three leads to external heatsink (t=1 s; $T_C = 25\text{ }^\circ\text{C}$ )	2500	V
$T_{stg}$ $T_J$	Storage temperature Max. operating junction temperature	-55 to 150 150	$^\circ\text{C}$

- Limited only by maximum temperature allowed.
- Pulse width limited by safe operating area.
- $I_{SD} \leq 15\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ,  $V_{DS\text{ peak}} \leq V_{(BR)DSS}$ ,  $V_{DD} = 80\% V_{(BR)DSS}$ .

**Table 3. Thermal data**

Symbol	Parameters	Value	Unit
$R_{thjc}$	Thermal resistance junction-case max.	4.17	$^\circ\text{C}/\text{W}$
$R_{thja}$	Thermal resistance junction-ambient max.	62.5	$^\circ\text{C}/\text{W}$

**Table 4. Avalanche characteristics**

Symbol	Parameters	Value	Unit
$I_{AS}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_{j\text{ max}}$ )	4	A
$E_{AS}$	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	115	mJ

## 2 Electrical characteristics

( $T_C = 25\text{ }^\circ\text{C}$  unless otherwise specified).

**Table 5. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	650			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS}=0$ )	$V_{DS} = 650\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 650\text{ V}$ , $T_C=0$			100	$\mu\text{A}$
$I_{GSS}$	Gate body leakage ( $V_{DS}=0$ )	$V_{GS} = \pm 25\text{ V}$ , $V_{DS}=0$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$I_D = 250\text{ }\mu\text{A}$ , $V_{GS} = V_{DS}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on- resistance	$I_D=7.5\text{ A}$ , $V_{GS}=10\text{ V}$		0.250	0.270	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{ISS}$	Input capacitance	$V_{DS} = 50\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	1280	-	pF
$C_{OSS}$	Output capacitance		-	110	-	pF
$C_{RSS}$	Reverse capacitance		-	10	-	pF
$C_{OSS\text{ eq}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0$ to $V_{GS} = 0$	-	260	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ , $I_D=0$	-	4.8	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 520\text{ V}$ , $I_D = 15\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 14</a> )	-	44	-	nC
$Q_{gs}$	Gate source charge		-	8	-	nC
$Q_{gd}$	Gate-drain charge		-	22	-	nC

1.  $C_{OSS\text{ eq}}$ : defined as a constant equivalent capacitance giving the same charging time as  $C_{OSS}$  when  $V_{DS}$  increases from 0 to 80 %  $V_{DSS}$ .

**Table 7. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325\text{ V}$ , $I_D=7.5\text{ A}$ $R_g=4.7\text{ }\Omega$ , $V_{GS}=10\text{ V}$ (see <a href="#">Figure 13</a> ) (see <a href="#">Figure 18</a> )	-	15	-	ns
$t_r$	Rise time		-	13.5	-	ns
$t_{d(off)}$	Turn-off-delay time		-	75	-	ns
$t_f$	Fall time		-	21	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source drain current		-		15	A
$I_{SDM}^{(1)}$	Source drain current (pulsed)		-		60	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 15 \text{ A}, V_{GS} = 0$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 15 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ (see <a href="#">Figure 15</a> )	-	455		ns
$Q_{rr}$	Reverse recovery charge		-	5.5		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	24.5		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 15 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}, T_j = 150 \text{ }^\circ\text{C}$ (see <a href="#">Figure 15</a> )	-	710		ns
$Q_{rr}$	Reverse recovery charge		-	8		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	24		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

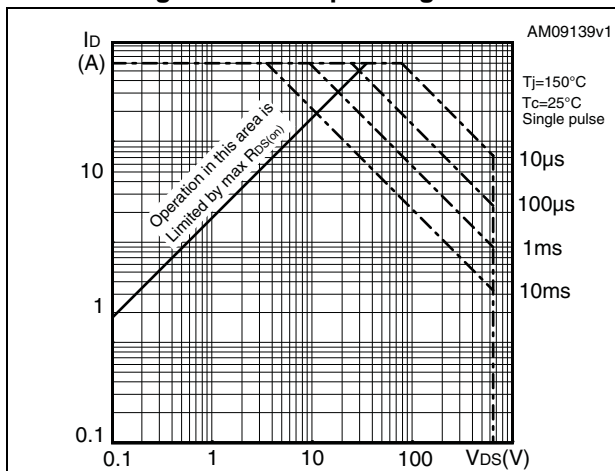


Figure 3. Thermal impedance

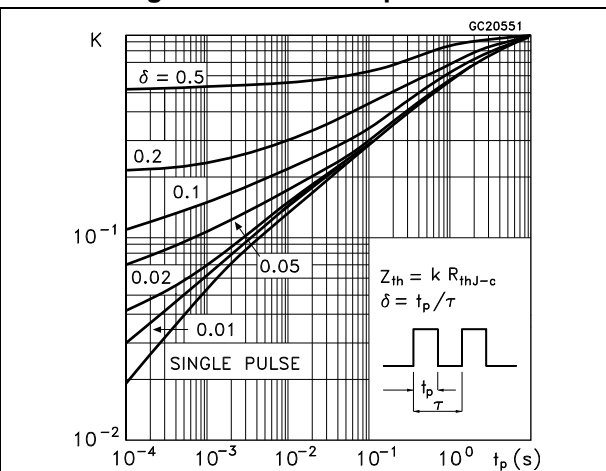


Figure 4. Output characteristics

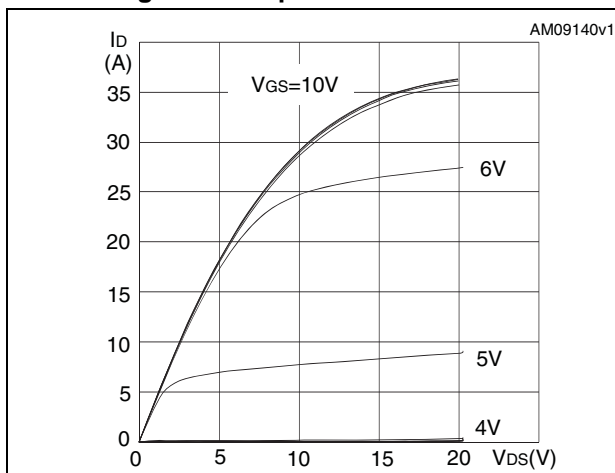


Figure 5. Transfer characteristics

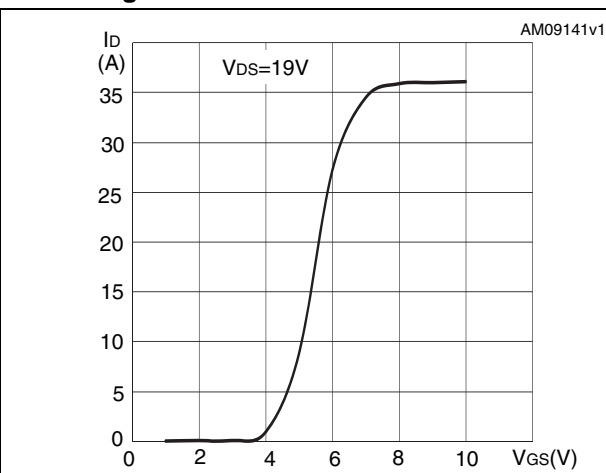


Figure 6. Normalized  $V_{(BR)DSS}$  vs temperature

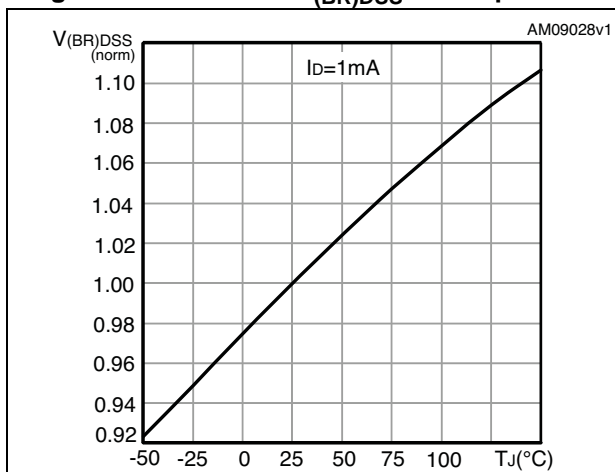


Figure 7. Static drain-source on-resistance

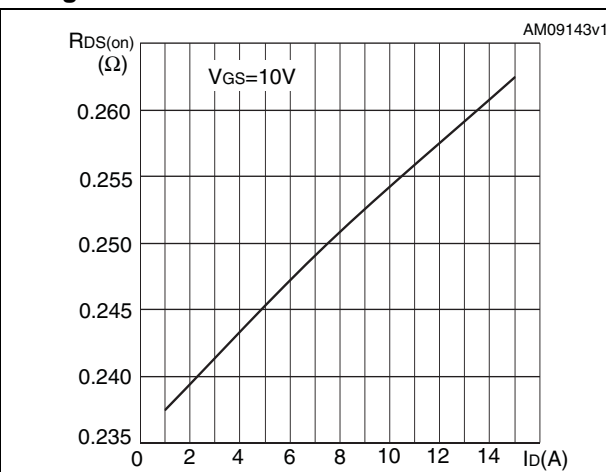


Figure 8. Gate charge vs gate-source voltage

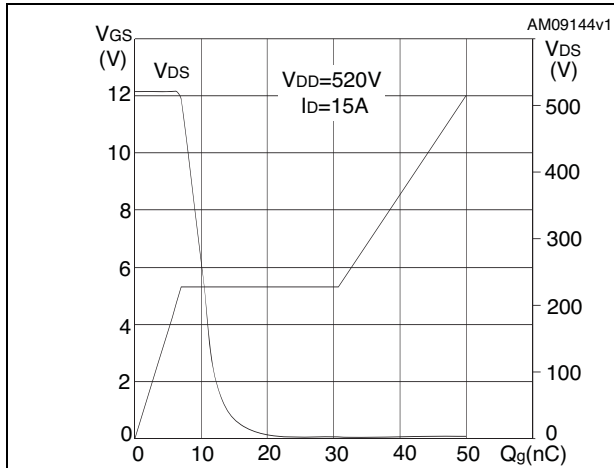


Figure 9. Capacitance variations

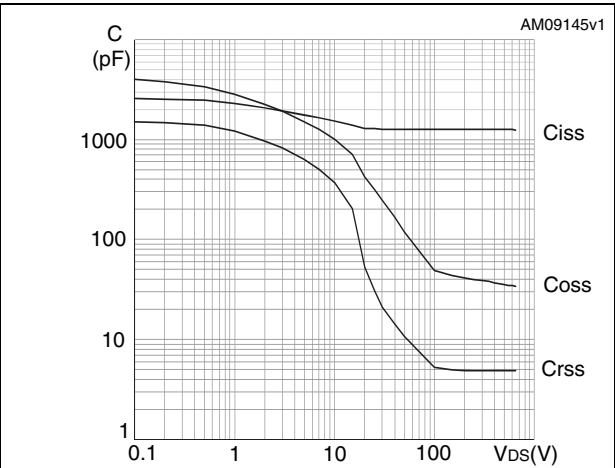


Figure 10. Normalized gate threshold voltage vs temperature

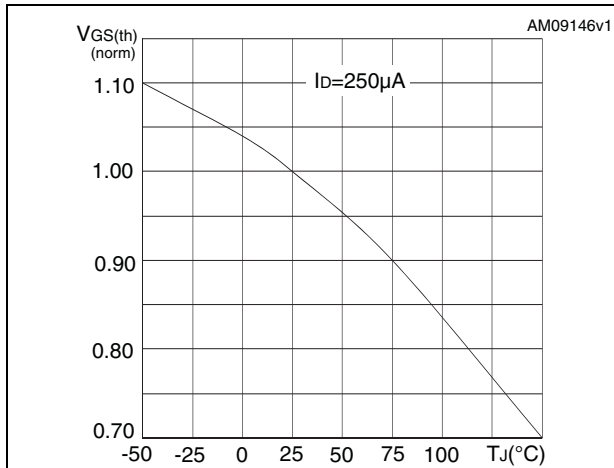


Figure 11. Normalized on-resistance vs temperature

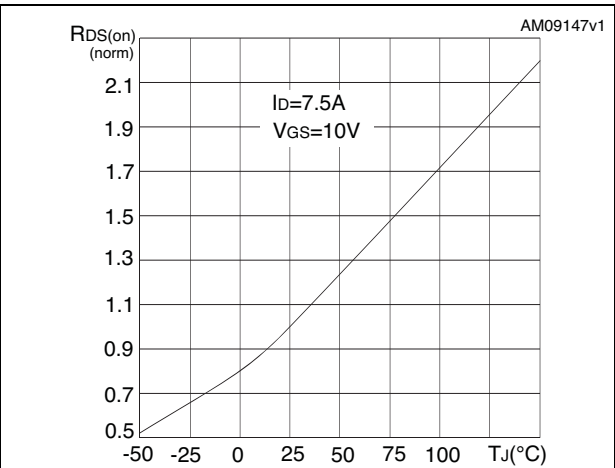
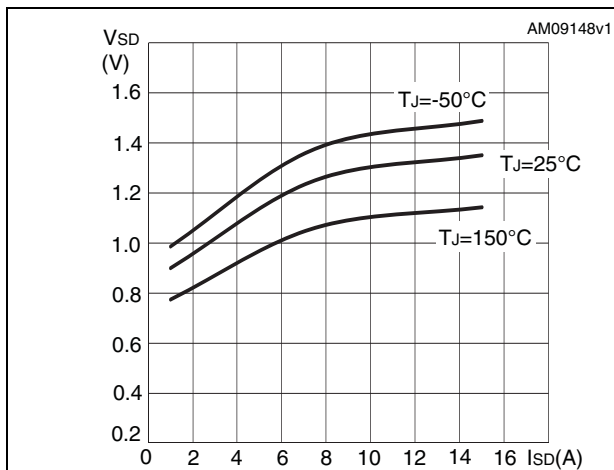


Figure 12. Source-drain diode forward characteristics



### 3 Test circuits

Figure 13. Switching times test circuit for resistive load

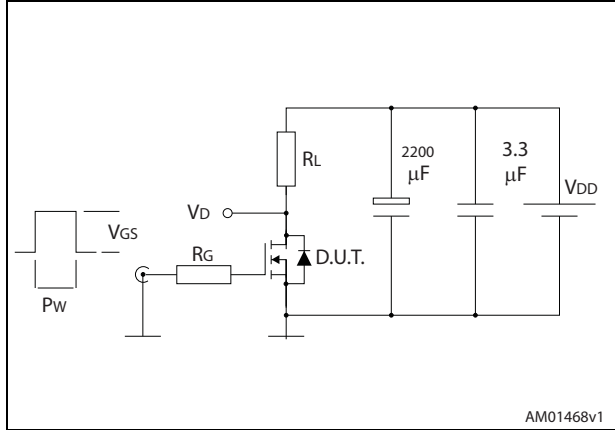


Figure 14. Gate charge test circuit

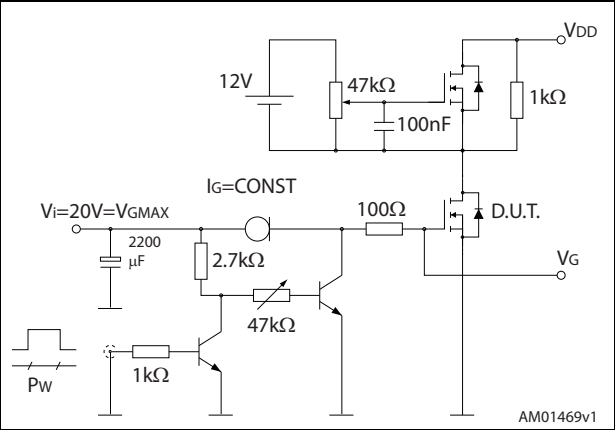


Figure 15. Test circuit for inductive load switching and diode recovery times

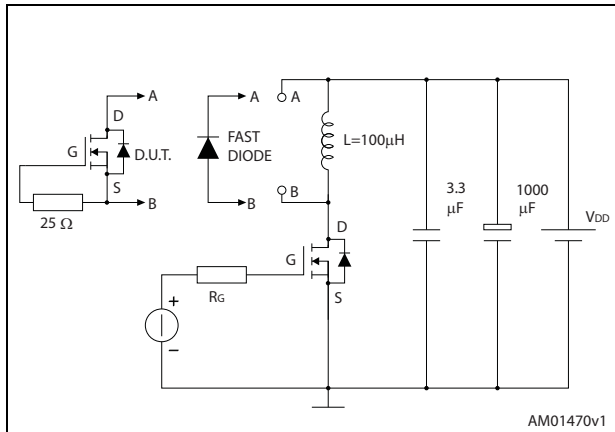


Figure 16. Unclamped inductive load test circuit

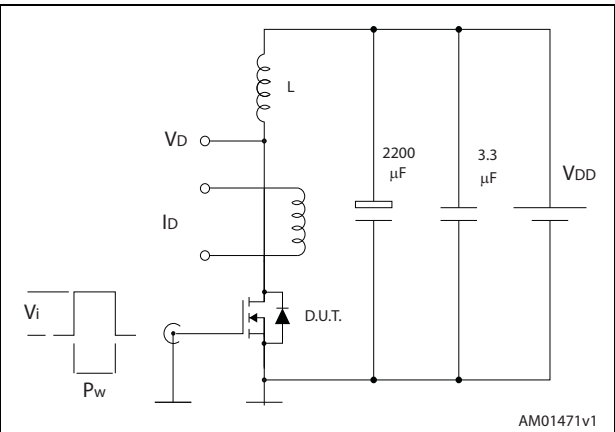


Figure 17. Unclamped inductive waveform

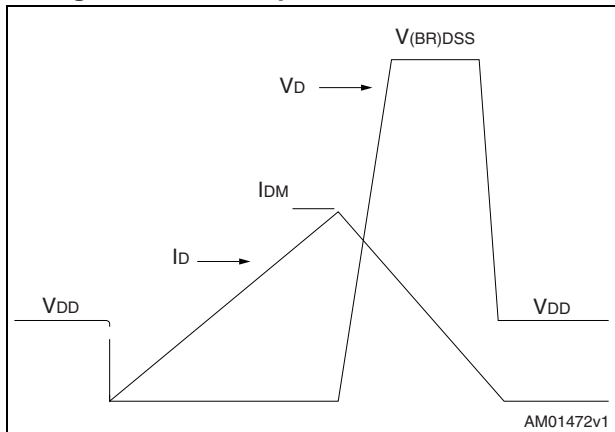
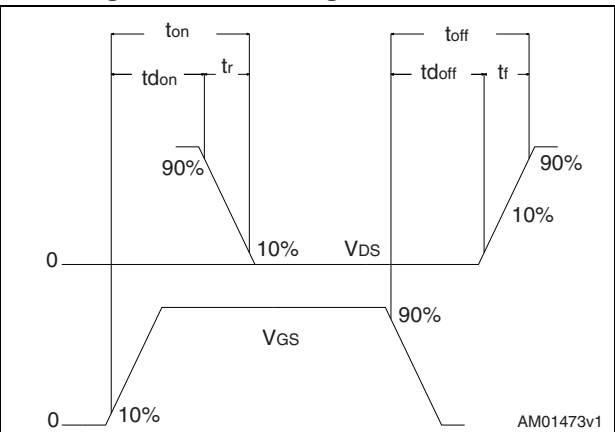


Figure 18. Switching time waveform



## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

Figure 19. I<sup>2</sup>PAKFP (TO-281) drawing

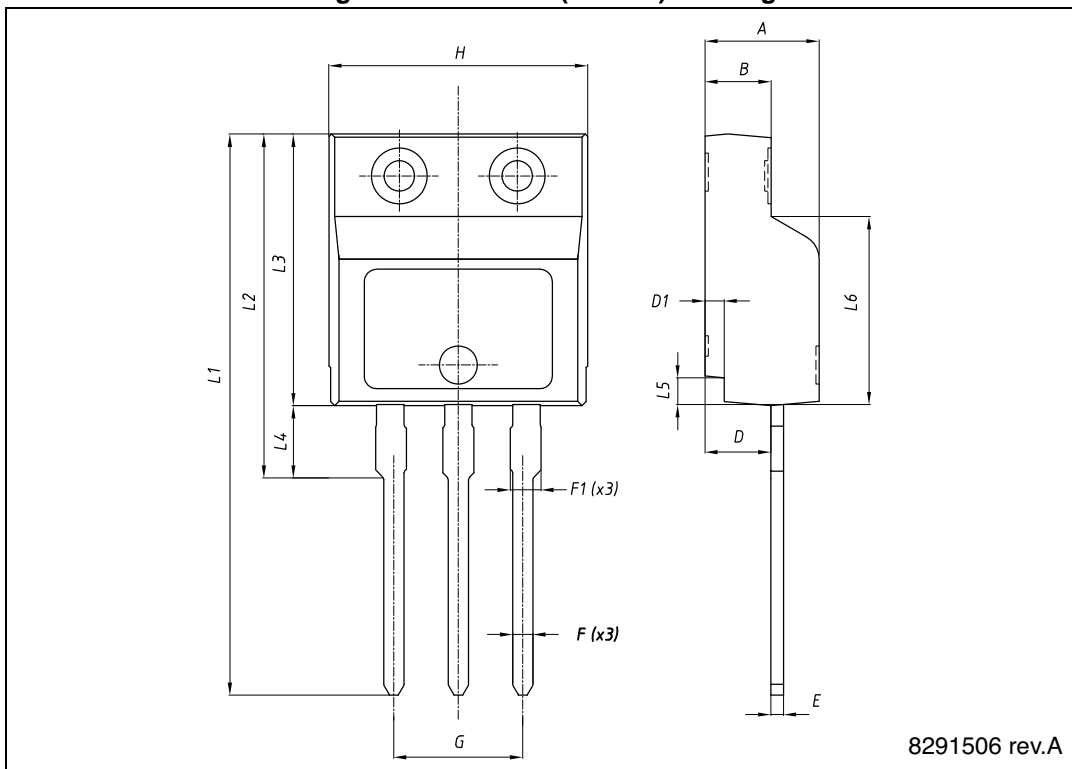


Table 9. I<sup>2</sup>PAKFP (TO-281) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
D1	0.65		0.85
E	0.45		0.70
F	0.75		1.00
F1			1.20
G	4.95	-	5.20
H	10.00		10.40
L1	21.00		23.00
L2	13.20		14.10
L3	10.55		10.85
L4	2.70		3.20
L5	0.85		1.25
L6	7.30		7.50

## 5 Revision history

Table 10. Revision history

Date	Revision	Changes
20-Dec-2013	1	Initial release.

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